

**eMMC Flash****3.3V 4 Gbyte****eMMC Flash Memory****Features**

- Compatible to JEDEC Embedded Multi Media Card (eMMC) Electrical Standard (5.1)
- Data bus width: 1bit(Default), 4bit and 8bit
- Not support large sector size (4KB)
- Interface power:  $V_{CCQ}$  (1.70V~1.95V or 2.7V~3.6V ), Memory power:  $V_{CC}$  ( 2.7V~3.6V )
- Temperature: Operation(-25°C~85°C), storage(-40°C~85°C)
- User Density:

Density	LBA(Hex)	LBA(Dec)	Capacity(Bytes)
4GB	0x73A000	7577600	3,879,731,200

**System Performance****Read/Write Performance**

Product ID	Read Sequential (MB/S)	Write Sequential (MB/S)
FC51L04SMSA-2.5BWGE	125	60

**Note:**

1. Values given for an 8-bit bus width, running HS400 mode from ESMT proprietary tool
2. Performance numbers might be subject to changes without notice.

**Capacity according to partition**

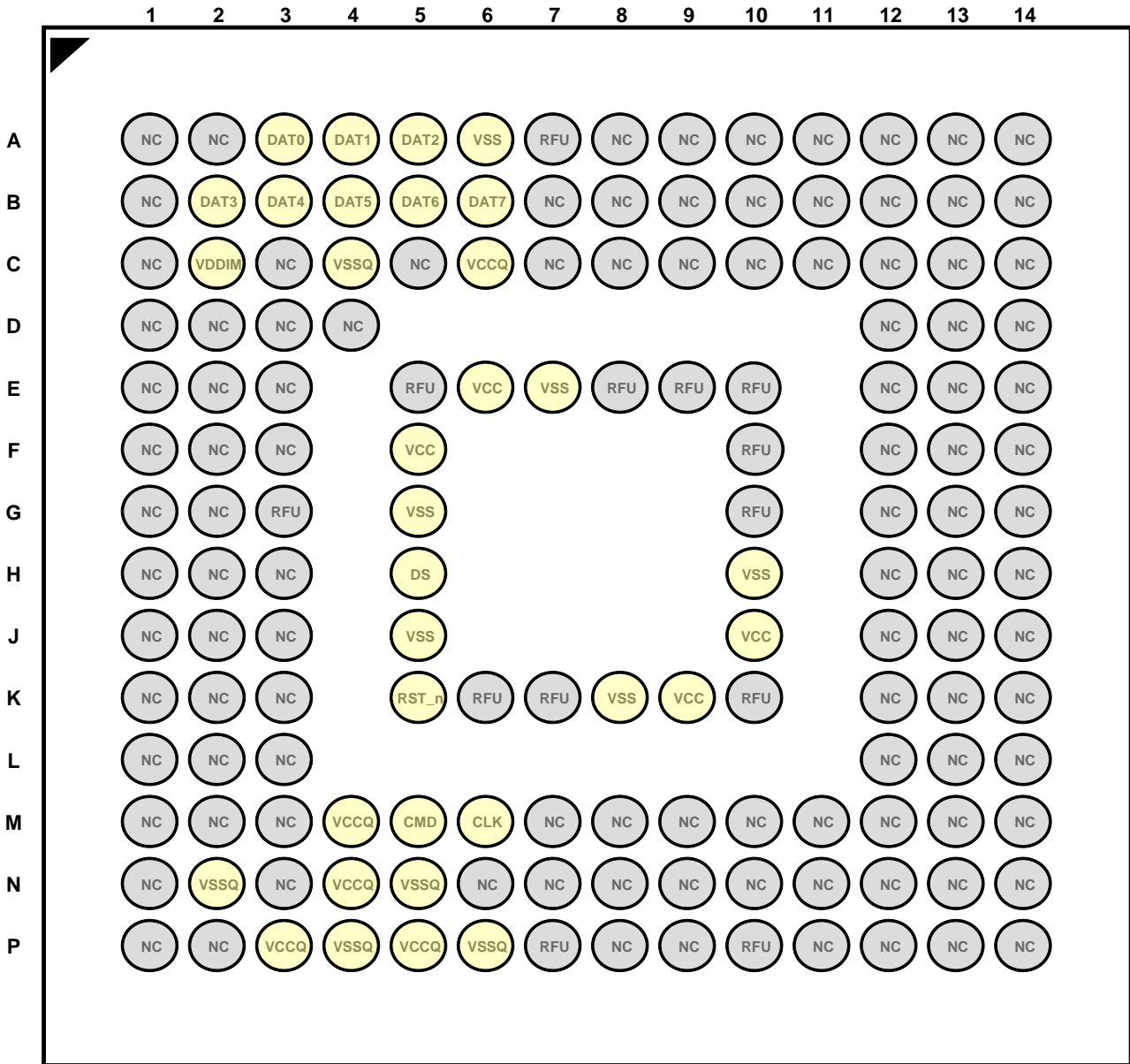
Capacity	Boot Partition 1	Boot Partition 2	RPMB
4GB	4096 KB	4096 KB	4096 KB

**Ordering Information**

Product ID	Speed	Package	Comments
FC51L04SMSA-2.5BWGE	200MHz	153 ball BGA	Pb-free

**Ball Configuration (Top View)**

(BGA 153 Ball, 11.5mmx13mmx1.0mm Body, 0.5mm Ball Pitch)



**Ball Descriptions**

Ball Name	Type <sup>1</sup>	Function
DAT0~DAT7	I/O/PP	Data Input/Output
DS	O/PP	Data Strobe
CLK	I	Clock
CMD	I/O/PP/OD	Command
VCC	S	Power Supply for Flash
VCCQ	S	Power Supply for Controller
VDDIM	-	Internal voltage node
VSS	S	Ground for Controller Flash
VSSQ	S	I/O Ground
RST_n	I	Reset
NC	NC	No Connection
RFU	-	Reserved For Future Use

**Note:**

1. I: input; O: Output; PP: push-pull; OD: open-drain; NC: Not connected (or logical high); S: power supply.

**eMMC Register Value****OCR Register**

OCR bit	Voltage window	Register Value
[6:0]	Reserved	000 0000b
[7]	1.70 – 1.95	1b
[14:8]	2.0-2.6	000 0000b
[23:15]	2.7-3.6	1 1111 1111b
[28:24]	Reserved	0 0000b
[30:29]	Access Mode	00b (byte mode), 10b (sector mode)
[31]	eMMC power up status bit	

**CID Register**

Name	Field	Width	CID-slice	CID Value
Manufacture ID	MID	8	[127:120]	ECh
Reserved		6	[119:114]	-
Card/BGA	CBX	2	[113:112]	01h
OEM/Application ID	OID	8	[111:104]	00h
Product name	PNM	48	[103:56]	534D30303030h
Product revision	PRV	8	[55:48]	10h
Product serial number	PSN	32	[47:16]	set at test
Manufacture date	MDT	8	[15:8]	set at test
CRC7 checksum	CRC	7	[7:1]	set at test
not used, always '1'	-	1	[0:0]	0x1

## CSD Register

Name	Field	Width	Cell Type	CSD-slice	CSD Value
CSD Structure	CSD-STRUCTURE	2	R	[127:126]	3h
System specification version	SPEC_VERS	4	R	[125:122]	4h
Reserved	-	2	R	[121:120]	-
Data read access-time 1	TAAC	8	R	[119:112]	2Fh
Data read access-time 2 in CLK cycles (NSAC*100)	NSAC	8	R	[111:104]	1h
Max. bus clock frequency	TRAN_SPEED	8	R	[103:96]	2Ah
Device command classes	CCC	12	R	[95:84]	DF5h
Max. read data block length	READ_BL_LEN	4	R	[83:80]	9h
Partial blocks for read allowed	READ_BL_PARTIAL	1	R	[79:79]	0h
Write block misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]	0h
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]	0h
DSR implemented	DSR_IMP	1	R	[76:76]	0h
Reserved	-	2	R	[75:74]	-
Device size	C_SIZE	12	R	[73:62]	FFFh
Max. read current@VDD min	VDD_R_CURR_MIN	3	R	[61:59]	6h
Max. read current@VDD max	VDD_R_CURR_MAX	3	R	[58:56]	6h
Max. write current@VDD min	VDD_W_CURR_MIN	3	R	[55:53]	6h
Max. write current@VDD max	VDD_W_CURR_MAX	3	R	[52:50]	6h
Device size multiplier	C_SIZE_MULT	3	R	[49:47]	7h
Erase group size	ERASE_GRP_SIZE	5	R	[46:42]	1Fh
Erase group size multiplier	ERASE_GRP_MULT	5	R	[41:37]	1Fh
Write Protect group size	WP_GRP_SIZE	5	R	[36:32]	1Fh
Write protect group enable	WP_GRP_ENABLE	1	R	[31:31]	1h
Manufacture default ECC	DEFAULT_ECC	2	R	[30:29]	0h
Write speed factor	R2W_FACTOR	3	R	[28:26]	1h
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]	9h
Partial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]	0h
Reserved	-	4	R	[20:17]	-
Content protection application	CONTENT_PROT_APP	1	R	[16:16]	0h
File format group	FILE_FORMAT_GRP	1	R/W	[15:15]	0h
Copy flag(OTP)	COPY	1	R/W	[14:14]	0h
Permanent write protection	PERM_WRITE_PROTECT	1	R/W	[13:13]	0h
Temporary write protection	TMP_WRITE_PROTECT	1	R/W/E	[12:12]	0h
File Format	FILE_FORMAT	2	R/W	[11:10]	0h
ECC code	ECC	2	R/W/E	[9:8]	0h
CRC	CRC	7	R/W/E	[7:1]	7h
Not used, always '1'	-	1	-	[0:0]	1h

## Extended CSD Register

Name	Field	Size	Cell Type	CSD- slice	CSD Value
Reserved <sup>1</sup>		6	TBD	[511:506]	-
Extended Security Commands Error	EXT_SECURITY_ERR	1	R	[505]	0h
Supported Command Sets	S_CMD_SET	1	R	[504]	1h
HPI features	HPI_FEATURES	1	R	[503]	3h
Background operations support	BKOPS_SUPPORT	1	R	[502]	1h
Max packed read commands	MAX_PACKED_READS	1	R	[501]	5h
Max packed write commands	MAX_PACKED_WRITES	1	R	[500]	3h
Data Tag Support	DATA_TAG_SUPPORT	1	R	[499]	1h
Tag Unit Size	TAG_UNIT_SIZE	1	R	[498]	1h
Tag Resources Size	TAG_RES_SIZE	1	R	[497]	0h
Context management capabilities	CONTEXT_CAPABILITIES	1	R	[496]	5h
Large Unit size	LARGE_UNIT_SIZE_M1	1	R	[495]	0h
Extended partitions attribute support	EXT_SUPPORT	1	R	[494]	3h
Supported modes	SUPPORTED_MODES	1	R	[493]	1h
FFU features	FFU_FEATURES	1	R	[492]	1h
Operation codes timeout	OPERATION_CODE_TIMEOUT	1	R	[491]	17h
FFU Argument	FFU_ARG	4	R	[490:487]	0h
Barrier support	BARRIER_SUPPORT	1	R	[486]	0h
Reserved <sup>1</sup>	-	177	TBD	[485:309]	-
CMD Queuing Support	CMDQ_SUPPORT	1	R	[308]	0h
CMD Queuing Depth	CMDQ_DEPTH	1	R	[307]	0h
Reserved <sup>1</sup>	-	1	TBD	[306]	-
Number of FW sectors correctly programmed	NUMBER_OF_FW_SECTORS_CORRECTLY_PROGRAMMED	4	R	[305:302]	0h
Vendor proprietary health report	VENDOR_PROPRIETARY_HEALTH_REPORT	32	R	[301:270]	0h
Device life time estimation type B	DEVICE_LIFE_TIME_EST_TYP_B	1	R	[269]	1h
Device life time estimation type A	DEVICE_LIFE_TIME_EST_TYP_A	1	R	[268]	1h
Pre EOL information	PRE_EOL_INFO	1	R	[267]	1h
Optimal read size	OPTIMAL_READ_SIZE	1	R	[266]	8h
Optimal write size	OPTIMAL_WRITE_SIZE	1	R	[265]	8h
Optimal trim unit size	OPTIMAL_TRIM_UNIT_SIZE	1	R	[264]	8h
Device version	DEVICE_VERSION	2	R	[263:262]	0h
Firmware version	FIRMWARE_VERSION	8	R	[261:254]	-
Power class for 200MHz, DDR at VCC= 3.6V	PWR_CL_DDR_200_360	1	R	[253]	0h

## Extended CSD Register - Continued

Name	Field	Size	Cell Type	CSD- slice	CSD Value
Cache size	CACHE_SIZE	4	R	[252:249]	80h
Generic CMD6 timeout	GENERIC_CMD6_TIME	1	R	[248]	32h
Power off notification(long) timeout	POWER_OFF_LONG_TIME	1	R	[247]	3Ch
Background operations status	BKOPS_STATUS	1	R	[246]	0h
Number of correctly programmed sectors	CORRECTLY_PRG_SECTORS_NUM	4	R	[245:242]	0h
1st initialization time after partitioning	INI_TIMEOUT_AP	1	R	[241]	1Eh
Cache Flushing Policy	ACHE_FLUSH_POLICY	1	R	[240]	0h
Power class for 52MHz, DDR at V <sub>CC</sub> = 3.6V	PWR_CL_DDR_52_360	1	R	[239]	0h
Power class for 52MHz, DDR at V <sub>CC</sub> = 1.95V	PWR_CL_DDR_52_195	1	R	[238]	0h
Power class for 200MHz at V <sub>CCQ</sub> =1.95V, V <sub>CC</sub> = 3.6V	PWR_CL_200_195	1	R	[237]	0h
Power class for 200MHz at V <sub>CCQ</sub> =1.3V, V <sub>CC</sub> = 3.6V	PWR_CL_200_130	1	R	[236]	0h
Minimum Write Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_W_8_52	1	R	[235]	0h
Minimum Read Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_R_8_52	1	R	[234]	0h
Reserved	-	1	TBD	[233]	
TRIM Multiplier	TRIM_MULT	1	R	[232]	2h
Secure Feature support	SEC_FEATURE_SUPPORT	1	R	[231]	55h
Secure Erase Multiplier	SEC_ERASE_MULT	1	R	[230]	1Bh
Secure TRIM Multiplier	SEC_TRIM_MULT	1	R	[229]	11h
Boot information	BOOT_INFO	1	R	[228]	7h
Reserved	-	1	TBD	[227]	-
Boot partition size	BOOT_SIZE_MULT1	1	R	[226]	20h
Access size	ACC_SIZE	1	R	[225]	1h
High-capacity erase unit size	HC_ERASE_GRP_SIZE	1	R	[224]	1h
High-capacity erase timeout	ERASE_TIMEOUT_MULT	1	R	[223]	20h
Reliable write sector count	REL_WR_SEC_C	1	R	[222]	1h
High-capacity write protect group size	HC_WP_GRP_SIZE	1	R	[221]	20h
Sleep current (VCC)	S_C_VCC	1	R	[220]	7h
Sleep current (VCCQ)	S_C_VCCQ	1	R	[219]	7h
Production state awareness timeout	PRODUCTION_STATE_AWARENESS_TIMEOUT	1	R	[218]	17h
Sleep/awake timeout	S_A_TIMEOUT	1	R	[217]	17h
Sleep Notification Timeout <sup>1</sup>	SLEEP_NOTIFICATION_TIME	1	R	[216]	11h

## Extended CSD Register - Continued

Name	Field	Size	Cell Type	CSD- slice	CSD Value
Sector Count	SEC_COUNT	4	R	[215:212]	73A000h
Reserved	-	1	TBD	[211]	0h
Minimum Write Performance for 8bit at 52MHz	MIN_PERF_W_8_52	1	R	[210]	0h
Minimum Read Performance for 8bit at 52MHz	MIN_PERF_R_8_52	1	R	[209]	0h
Minimum Write Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_W_8_26_4_52	1	R	[208]	0h
Minimum Read Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_R_8_26_4_52	1	R	[207]	0h
Minimum Write Performance for 4bit at 26MHz	MIN_PERF_W_4_26	1	R	[206]	0h
Minimum Read Performance for 4bit at 26MHz	MIN_PERF_R_4_26	1	R	[205]	0h
Reserved	-	1	TBD	[204]	-
Power class for 26MHz at 3.6V 1 R	PWR_CL_26_360	1	R	[203]	0h
Power class for 52MHz at 3.6V 1 R	PWR_CL_52_360	1	R	[202]	0h
Power class for 26MHz at 1.95V 1 R	PWR_CL_26_195	1	R	[201]	0h
Power class for 52MHz at 1.95V 1 R	PWR_CL_52_195	1	R	[200]	0h
Partition switching timing	PARTITION_SWITCH_TIME	1	R	[199]	5h
Out-of-interrupt busy timing	OUT_OF_INTERRUPT_TIME	1	R	[198]	19h
I/O Driver Strength	DRIVER_STRENGTH	1	R	[197]	Fh
Device type	DEVICE_TYPE	1	R	[196]	57h
Reserved <sup>1</sup>	-	1	TBD	[195]	-
CSD STRUCTURE	CSD_STRUCTURE	1	R	[194]	2h
Reserved <sup>1</sup>	-	1	TBD	[193]	-
Extended CSD revision	EXT_CSD_REV	1	R	[192]	8h
Modes Segment	-	-	-	-	-
Command set	CMD_SET	1	R/W/E_P	[191]	0h
Reserved <sup>1</sup>	-	1	TBD	[190]	-
Command set revision	CMD_SET_REV	1	R	[189]	0h
Reserved <sup>1</sup>	-	1	TBD	[188]	-
Power class	POWER_CLASS	1	R/W/E_P	[187]	0h
Reserved <sup>1</sup>	-	1	TBD	[186]	-
High-speed interface timing	HS_TIMING	1	R/W/E_P	[185]	0h
Reserved <sup>1</sup> Strobe Support	-	1	<del>TBD</del> R	[184]	0h 1h
Bus width mode	BUS_WIDTH	1	W/E_P	[183]	0h
Reserved <sup>1</sup>	-	1	TBD	[182]	-
Erased memory content	ERASED_MEM_CONT	1	R	[181]	0h
Reserved <sup>1</sup>	-	1	TBD	[180]	-



**Extended CSD Register - Continued**

Name	Field	Size	Cell Type	CSD- slice	CSD Value
Partition configuration	PARTITION_CONFIG	1	R/W/E & R/W/E_P	[179]	0h
Boot config protection	BOOT_CONFIG_PROT	1	R/W & R/W/C_P	[178]	0h
Boot bus Conditions	BOOT_BUS_CONDITIONS	1	R/W/E	[177]	0h
Reserved <sup>1</sup>	-	1	TBD	[176]	-
High-density erase group definition	ERASE_GROUP_DEF	1	R/W/E_P	[175]	0h
Boot write protection status registers	BOOT_WP_STATUS	1	R	[174]	0h
Boot area write protection register	BOOT_WP	1	R/W & R/W/C_P	[173]	0h
Reserved <sup>1</sup>	-	1	TBD	[172]	-
User area write protection register	USER_WP	1	R/W, R/W/C_P & R/W/E_P	[171]	0h
Reserved <sup>1</sup>	-	1	TBD	[170]	-
FW configuration	FW_CONFIG	1	R/W	[169]	0h
RPMB Size	RPMB_SIZE_MULT	1	R	[168]	20h
Write reliability setting register	WR_REL_SET	1	R/W	[167]	0h
Write reliability parameter register	WR_REL_PARAM	1	R	[166]	15h
Start Sanitize operation	SANITIZE_START	1	W/E_P	[165]	0h
Manually start background operations	BKOPS_START	1	W/E_P	[164]	0h
Enable background operations handshake	BKOPS_EN	1	R/W	[163]	0h
H/W reset function	RST_n_FUNCTION	1	R/W	[162]	0h
HPI management	HPI_MGMT	1	R/W/E_P	[161]	0h
Partitioning Support	PARTITIONING_SUPPORT	1	R	[160]	7h
Max Enhanced Area Size	MAX_ENH_SIZE_MULT	3	R	[159:157]	73h
Partitions attribute	PARTITIONS_ATTRIBUTE	1	R/W	[156]	0h
Partitioning Setting	PARTITION_SETTING_COMPLETED	1	R/W	[155]	0h
General Purpose Partition Size	GP_SIZE_MULT	12	R/W	[154:143]	0h
Enhanced User Data Area Size	ENH_SIZE_MULT	3	R/W	[142:140]	0h
Enhanced User Data Start Address	ENH_START_ADDR	4	R/W	[139:136]	0h
Reserved <sup>1</sup>	-	1	TBD	[135]	-
Bad Block Management mode	SEC_BAD_BLK_MGMNT	1	R/W	[134]	0h
Production state awareness	PRODUCTION_STATE_AWARENESS	1	R/W/E	[133]	0h
Package Case Temperature is controlled	TCASE_SUPPORT	1	W/E_P	[132]	0h

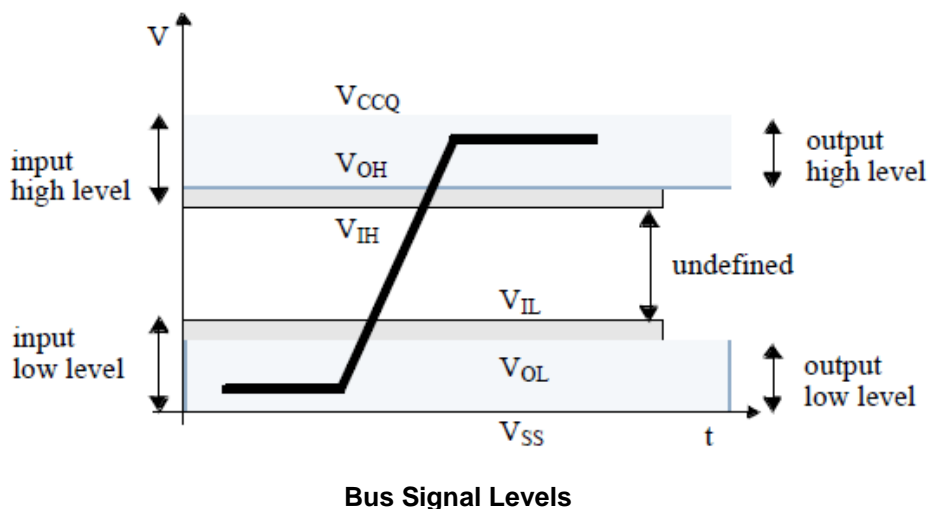
## Extended CSD Register - Continued

Name	Field	Size	Cell Type	CSD- slice	CSD Value
Periodic Wake-up	PERIODIC_WAKEUP	1	R/W/E	[131]	0h
Program CID/CSD in DDR mode support	PROGRAM_CID_CSD_DDR_SUPPORT	1	R	[130]	1h
Reserved <sup>1</sup>	-	2	-	[129:128]	-
Vendor Specific Fields	VENDOR_SPECIFIC_FIELD	64	vendor specific	[127:64]	0h
Native sector size	NATIVE_SECTOR_SIZE	1	R	[63]	0h
Sector size emulation	USE_NATIVE_SECTOR	1	R/W	[62]	0h
Sector size	DATA_SECTOR_SIZE	1	R	[61]	0h
1st initialization after disabling sector size emulation	INI_TIMEOUT_EMU	1	R	[60]	0h
Class 6 commands control	CLASS_6_CTRL	1	R/W/E_P	[59]	0h
Number of addressed group to be Released	DYNCAP_NEEDED	1	R	[58]	0h
Exception events control	EXCEPTION_EVENTS_CTRL	2	R/W/E_P	[57:56]	0h
Exception events status	EXCEPTION_EVENTS_STATUS	2	R	[55:54]	0h
Extended Partitions Attribute	EXT_PARTITIONS_ATTRIBUTE	2	R/W	[53:52]	0h
Context configuration	CONTEXT_CONF	15	R/W/E_P	[51:37]	0h
Packed command status	PACKED_COMMAND_STATUS	1	R	[36]	0h
Packed command failure index	PACKED_FAILURE_INDEX	1	R	[35]	0h
Power Off Notification	POWER_OFF_NOTIFICATION	1	R/W/E_P	[34]	0h
Control to turn the Cache ON/OFF	CACHE_CTRL	1	R/W/E_P	[33]	0h
Flushing of the cache	FLUSH_CACHE	1	W/E_P	[32]	0h
Reserved <sup>1</sup>	-	1	TBD	[31]	0h
Mode config	MODE_CONFIG	1	R/W/E_P	[30]	0h
Mode operation codes	MODE_OPERATION_CODES	1	W/E_P	[29]	0h
Reserved <sup>1</sup>	-	2	TBD	[28:27]	-
FFU status	FFU_STATUS	1	R	[26]	0h
Pre loading data size	PRE_LOADING_DATA_SIZE	4	R/W/E_P	[25:22]	0h
Max pre loading data size	MAX_PRE_LOADING_DATA_SIZE	4	R	[21:18]	3A6000h

**Extended CSD Register - Continued**

<b>Name</b>	<b>Field</b>	<b>Size</b>	<b>Cell Type</b>	<b>CSD- slice</b>	<b>CSD Value</b>
Product state awareness enablement	PRODUCT_STATE_AWARENESS_ENABLEMENT	1	R/W/E & R	[17]	3h
Secure Removal Type	SECURE_REMOVAL_TYPE	1	R/W & R	[16]	9h
Command Queue Mode Enable	CMDQ_MODE_EN	1	R/W/E_P	[15]	0h
Reserved <sup>1</sup>	-	15	TBD	[14:0]	-

## Bus Signal Levels

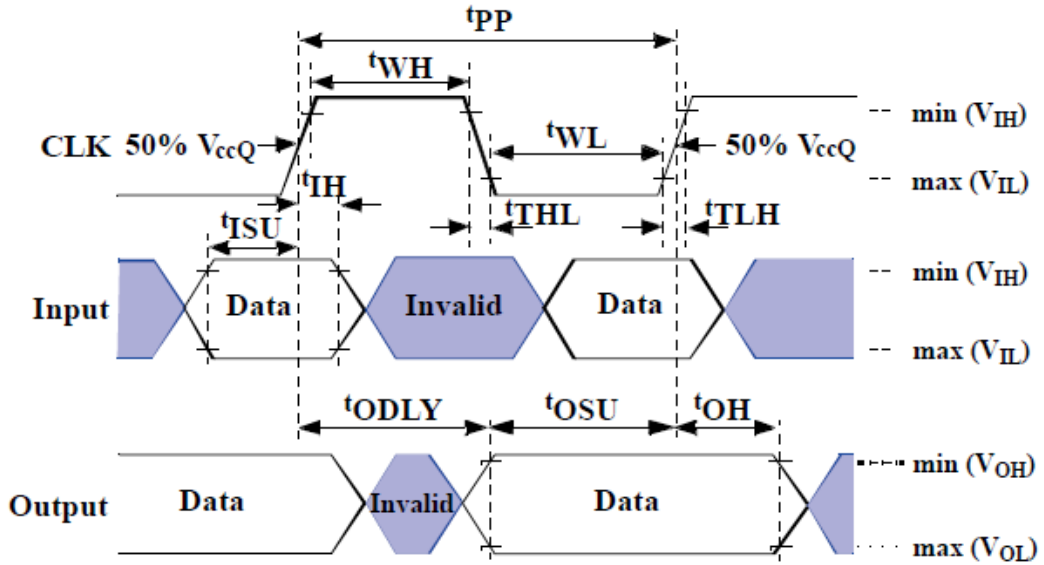


## Bus Signal Levels

Parameter	Symbol	Min	Max	Unit	Remark
<b>Open-drain bus signal level</b>					
Output HIGH voltage	$V_{OH}$	$V_{CCQ}-0.2$		V	
Output LOW voltage	$V_{OL}$		0.3	V	$I_{OL} = 2mA$
<b>Push-pull bus signal level (2.7V~3.6V <math>V_{CCQ}</math>)</b>					
Output HIGH voltage	$V_{OH}$	$0.75 * V_{CCQ}$		V	$I_{OH} = -100\mu A @ VDD \text{ min}$
Output LOW voltage	$V_{OL}$		$0.125 * V_{CCQ}$	V	$I_{OL} = 100\mu A @ VDD \text{ min}$
Input HIGH voltage	$V_{IH}$	$0.625 * V_{CCQ}$	$V_{CCQ} + 0.3$	V	
Input LOW voltage	$V_{IL}$	$V_{SS} - 0.3$	$0.25 * V_{CCQ}$	V	
<b>Push-pull bus signal level (1.70V~1.95V <math>V_{CCQ}</math>)</b>					
Output HIGH voltage	$V_{OH}$	$V_{CCQ} - 0.45$		V	$I_{OH} = - 2mA$
Output LOW voltage	$V_{OL}$		0.45	V	$I_{OL} = 2mA$
Input HIGH voltage	$V_{IH}$	$0.65 * V_{CCQ}$	$V_{CCQ} + 0.3$	V	
Input LOW voltage	$V_{IL}$	$V_{SS} - 0.3$	$0.35 * V_{CCQ}$	V	

**Bus Timing**

**Device Interface Timings**



Data must always be sampled on the rising edge of the clock.

**Timing diagram: data input/output**

## High-Speed Device Interface Timing

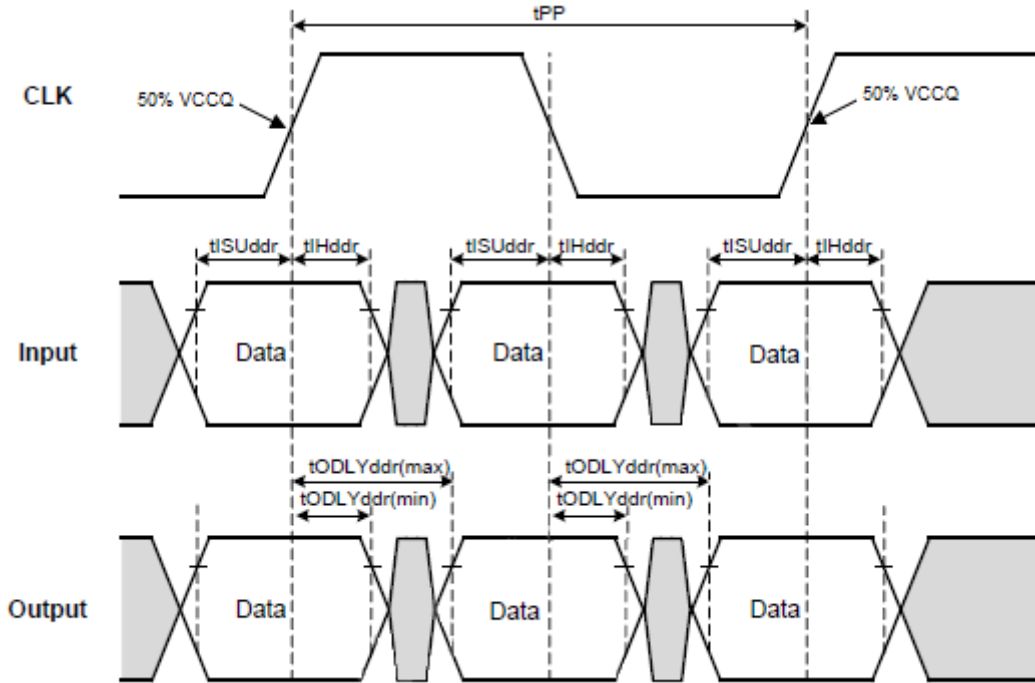
Parameter	Symbol	Min	Max	Unit	Remark
<b>Clock CLK<sup>1</sup></b>					
Clock frequency data transfer mode (PP) <sup>2</sup>	f <sub>PP</sub>	0	52 <sup>3</sup>	MHz	CL ≤ 30pF Tolerance: +100kHz
Clock frequency identification mode (OD)	f <sub>OD</sub>	0	400	kHz	Tolerance: +20kHz
Clock high time	t <sub>WH</sub>	6.5	-	ns	CL ≤ 30pF
Clock low time	t <sub>WL</sub>	6.5	-	ns	CL ≤ 30pF
Clock rise time <sup>4</sup>	t <sub>TLH</sub>	-	3	ns	CL ≤ 30pF
Clock fall time	t <sub>THL</sub>	-	3	ns	CL ≤ 30pF
<b>Inputs CMD, DAT (referenced to CLK)</b>					
Input set-up time	t <sub>ISU</sub>	3	-	ns	CL ≤ 30pF
Input hold time	t <sub>IH</sub>	3	-	ns	CL ≤ 30pF
<b>Outputs CMD, DAT (referenced to CLK)</b>					
Output delay time during data transfer	t <sub>ODLY</sub>	-	13.7	ns	CL ≤ 30pF
Output hold time	t <sub>OH</sub>	2.5	-	ns	CL ≤ 30pF
Signal rise time <sup>5</sup>	t <sub>RISE</sub>	-	3	ns	CL ≤ 30pF
Signal fall time	t <sub>FALL</sub>	-	3	ns	CL ≤ 30pF
<b>Note:</b>					
<ol style="list-style-type: none"> <li>1. CLK timing is measured at 50% of V<sub>CCQ</sub>.</li> <li>2. A eMMC shall support the full frequency range from 0 Mhz - 26 Mhz, or 0 MHz - 52 MHz</li> <li>3. Device can operate as high-speed Device interface timing at 26 MHz clock frequency.</li> <li>4. CLK rise and fall times are measured by min (V<sub>IH</sub>) and max (V<sub>IL</sub>).</li> <li>5. Inputs CMD, DAT rise and fall times are measured by min (V<sub>IH</sub>) and max (V<sub>IL</sub>), and outputs CMD, DAT rise and fall times are measured by min (V<sub>OH</sub>) and max (V<sub>OL</sub>).</li> </ol>					

## Backward Compatible Device Interface Timing

Parameter	Symbol	Min	Max	Unit	Remark <sup>1</sup>
<b>Clock CLK<sup>2</sup></b>					
Clock frequency data transfer mode (PP) <sup>3</sup>	f <sub>PP</sub>	0	26	MHz	CL ≤ 30pF
Clock frequency identification mode (OD)	f <sub>OD</sub>	0	400	kHz	-
Clock high time	t <sub>WH</sub>	10	-	ns	CL ≤ 30pF
Clock low time	t <sub>WL</sub>	10	-	ns	CL ≤ 30pF
Clock rise time <sup>4</sup>	t <sub>TLH</sub>	-	10	ns	CL ≤ 30pF
Clock fall time	t <sub>THL</sub>	-	10	ns	CL ≤ 30pF
<b>Inputs CMD, DAT (referenced to CLK)</b>					
Input set-up time	t <sub>ISU</sub>	3	-	ns	CL ≤ 30pF
Input hold time	t <sub>IH</sub>	3	-	ns	CL ≤ 30pF
<b>Outputs CMD, DAT (referenced to CLK)</b>					
Output delay time during data transfer <sup>5</sup>	t <sub>ODLY</sub>	11.7	-	ns	CL ≤ 30pF
Output hold time <sup>5</sup>	t <sub>OH</sub>	8.3	-	ns	CL ≤ 30pF
<b>Note:</b>					
<ol style="list-style-type: none"> <li>The Device must always start with the backward-compatible interface timing. The timing mode can be switched to high-speed interface timing by the host sending the SWITCH command (CMD6) with the argument for high-speed interface select.</li> <li>CLK timing is measured at 50% of V<sub>CCQ</sub>.</li> <li>For compatibility with Devices that support the v4.2 standard or earlier, host should not use &gt; 26 MHz before switching to high-speed interface timing.</li> <li>CLK rise and fall times are measured by min (V<sub>IH</sub>) and max (V<sub>IL</sub>).</li> <li>t<sub>OSU</sub> and t<sub>OH</sub> are defined as values from clock rising edge. However, there may be Devices or devices which utilize clock falling edge to output data in backward compatibility mode. Therefore, it is recommended for hosts either to set t<sub>WL</sub> value as long as possible within the range which will not go over t<sub>CK-tOH(min)</sub> in the system or to use slow clock frequency, so that host could have data set up margin for those devices. In this case, each device which utilizes clock falling edge might show the correlation either between t<sub>WL</sub> and t<sub>OSU</sub> or between t<sub>CK</sub> and t<sub>OSU</sub> for the device in its own datasheet as a note or its' application notes.</li> </ol>					

**Dual Data Rate Interface Timings**

**Bus Timing in Dual Data Rate Mode**





## High-speed Dual Data Rate Interface Timing

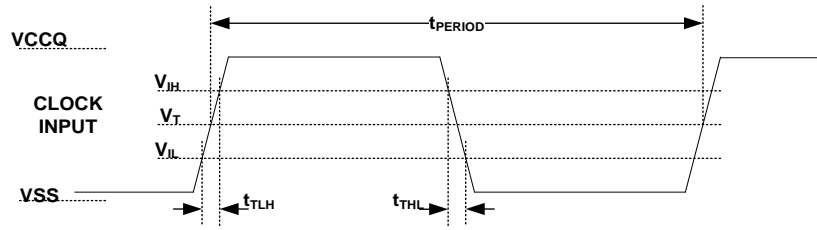
Parameter	Symbol	Min	Max	Unit	Remark
<b>Input CLK<sup>1</sup></b>					
Clock duty cycle	-	45	55	%	Includes jitter, phase noise
Clock rise time	$t_{TLH}$	-	3	ns	$CL \leq 30pF$
Clock fall time	$t_{THL}$	-	3	ns	$CL \leq 30pF$
<b>Input CMD (referenced to CLK-SDR mode)</b>					
Input set-up time	$t_{ISUddr}$	3	-	ns	$CL \leq 20pF$
Input hold time	$t_{IHddr}$	3	-	ns	$CL \leq 20pF$
<b>Output CMD (referenced to CLK-SDR mode)</b>					
Output delay time during data transfer	$t_{ODLY}$	-	13.7	ns	$CL \leq 20pF$
Output hold time	$t_{OH}$	2.5	-	ns	$CL \leq 20pF$
Signal rise time	$t_{RISE}$	-	3	ns	$CL \leq 20pF$
Signal fall time	$t_{FALL}$	-	3	ns	$CL \leq 20pF$
<b>Input DAT (referenced to CLK-DDR mode)</b>					
Input set-up time	$t_{ISUddr}$	2.5	-	ns	$CL \leq 20pF$
Input hold time	$t_{IHddr}$	2.5	-	ns	$CL \leq 20pF$
<b>Output DAT (referenced to CLK-DDR mode)</b>					
Output delay time during data transfer	$t_{ODLYddr}$	1.5	7	ns	$CL \leq 20pF$
Signal rise time (DAT0-7) <sup>2</sup>	$t_{RISE}$	-	2	ns	$CL \leq 20pF$
Signal fall time (DAT0-7)	$t_{FALL}$	-	2	ns	$CL \leq 20pF$

### Notes:

1. CLK timing is measured at 50% of  $V_{CCQ}$ .
2. Inputs DAT rise and fall times are measured by min ( $V_{IH}$ ) and max ( $V_{IL}$ ), and outputs DAT rise and fall times are measured by min ( $V_{OH}$ ) and max ( $V_{OL}$ ).

**Bus Timing Specification in HS200 mode**

**HS200 Device Clock Timing**



**HS200 Device Clock Timing**

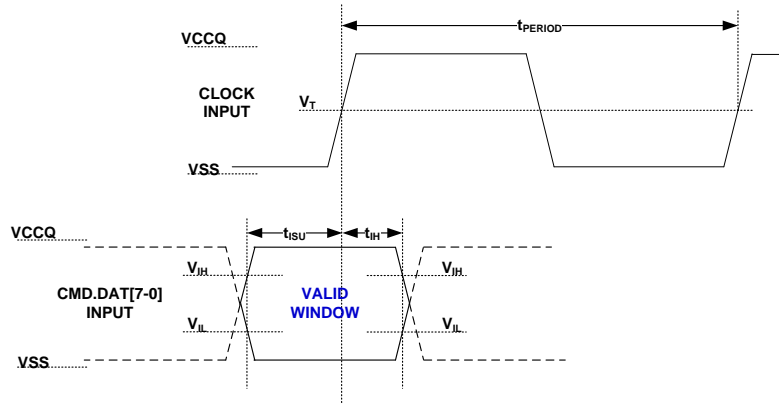
Note1:  $V_{IH}$  denote  $V_{IH(min.)}$  and  $V_{IL}$  denotes  $V_{IL(max.)}$ .

Note2:  $V_T=0.975V$  - Clock Threshold ( $V_{CCQ} = 1.8V$ ) and  $V_T=0.65V$  - Clock Threshold ( $V_{CCQ} = 1.2V$ ), indicates clock reference point for timing measurements.

**HS200 Device Clock Timing**

Symbol	Min.	Max.	Unit	Remark
$t_{PERIOD}$	5	-	ns	200MHz (Max.), between rising edges
$t_{TLH}, t_{THL}$	-	$0.2 \cdot t_{PERIOD}$	ns	$t_{TLH}, t_{THL} < 1ns$ (max.) at 200MHz, $C_{DEVICE}=6pF$ , The absolute maximum value of $t_{TLH}, t_{THL}$ is 10ns regardless of clock frequency.
Duty Cycle	30	70	%	

**HS200 Device Input Timing**



**HS200 Device Input Timing**

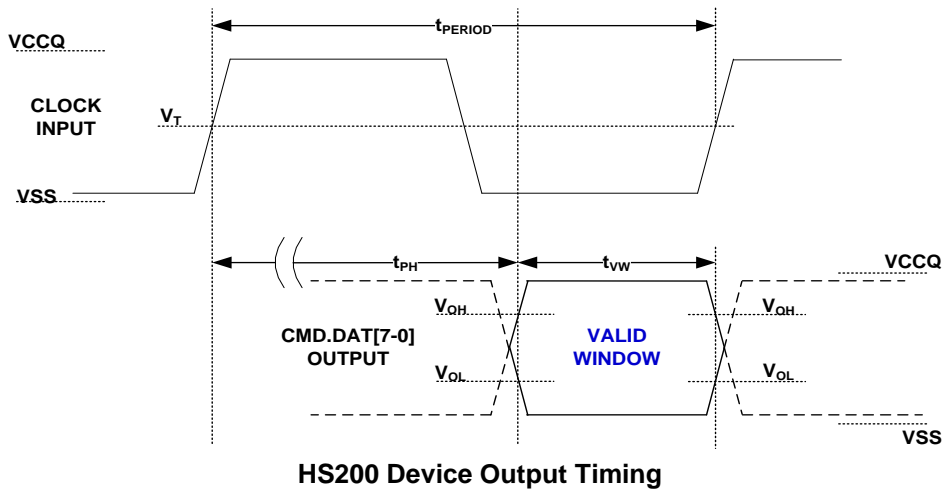
Note1:  $t_{ISU}$  and  $t_{IH}$  are measured at  $V_{IL(max)}$  and  $V_{IH(min)}$ .

Note2:  $V_{IH}$  denote  $V_{IH(min)}$  and  $V_{IL}$  denotes  $V_{IL(max)}$ .

**HS200 Device Input Timing**

Symbol	Min.	Max.	Unit	Remark
$t_{ISU}$	1.40	-	ns	$C_{DEVICE} \leq 6pF$
$t_{IH}$	0.8		ns	$C_{DEVICE} \leq 6pF$

**HS200 Device Output Timing**



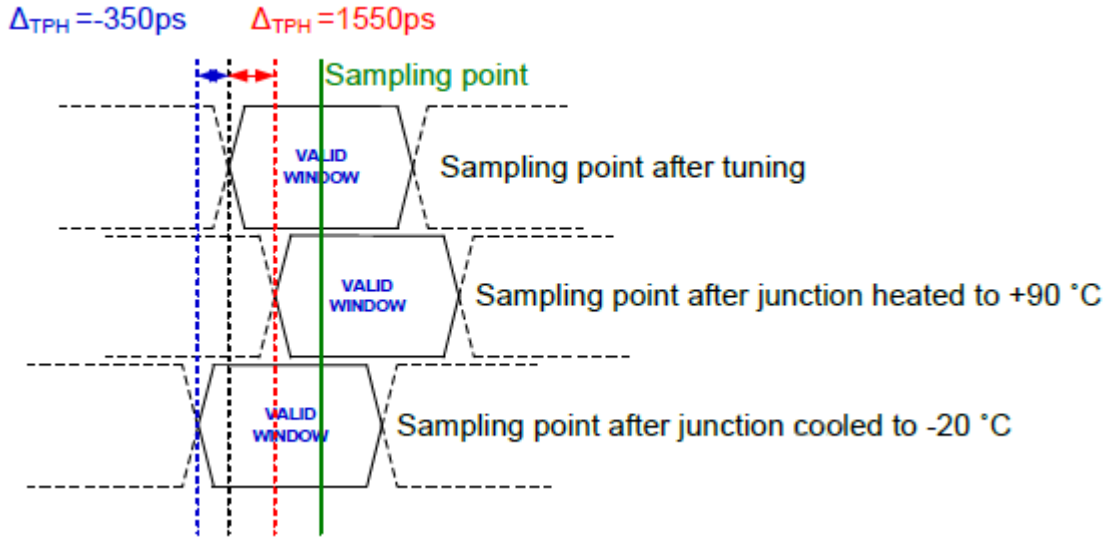
Note:  $V_{OH}$  denotes  $V_{OH(min.)}$  and  $V_{OL}$  denotes  $V_{OL(max.)}$ .

**HS200 Device Output Timing**

Symbol	Min.	Max.	Unit	Remark
$t_{PH}$	0	2	UI	Device output momentary phase from CLK input to CMD or DAT lines output. Does not include a long term temperature drift.
$\Delta T_{PH}$	-350 ( $\Delta T = -20$ deg.C)	+1550 ( $\Delta T = 90$ deg.C)	ps	Delay variation due to temperature change after tuning. Total allowable shift of output valid window ( $T_{VW}$ ) from last system Tuning procedure $\Delta T_{PH}$ is 2600ps for $\Delta T$ from -25 deg.C to 125 deg.C during operation.
$t_{VW}$	0.575	-	UI	$t_{VW} = 2.88ns$ at 200MHz Using test circuit in Figure 6 including skew among CMD and DAT lines created by the Device. Host path may add Signal Integrity induced noise, skews, etc. Expected $T_{VW}$ at Host input is larger than 0.475UI.

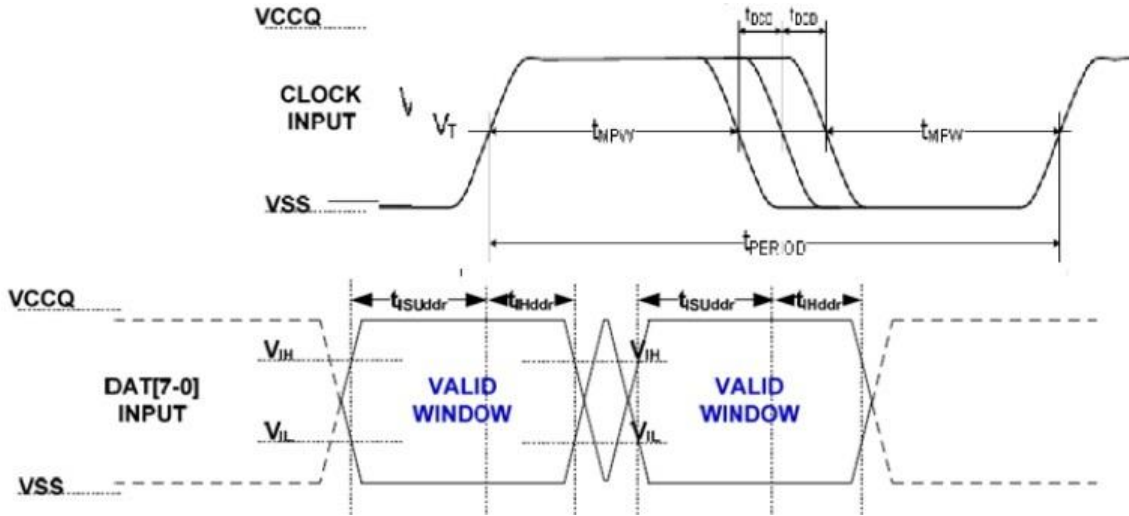
Note: Unit Interval (UI) is one bit nominal time. For example, UI=5ns at 200MHz.

**t<sub>PH</sub> Consideration**



**Bus Timing Specification in HS400 mode**

**HS400 Device Input Timing**

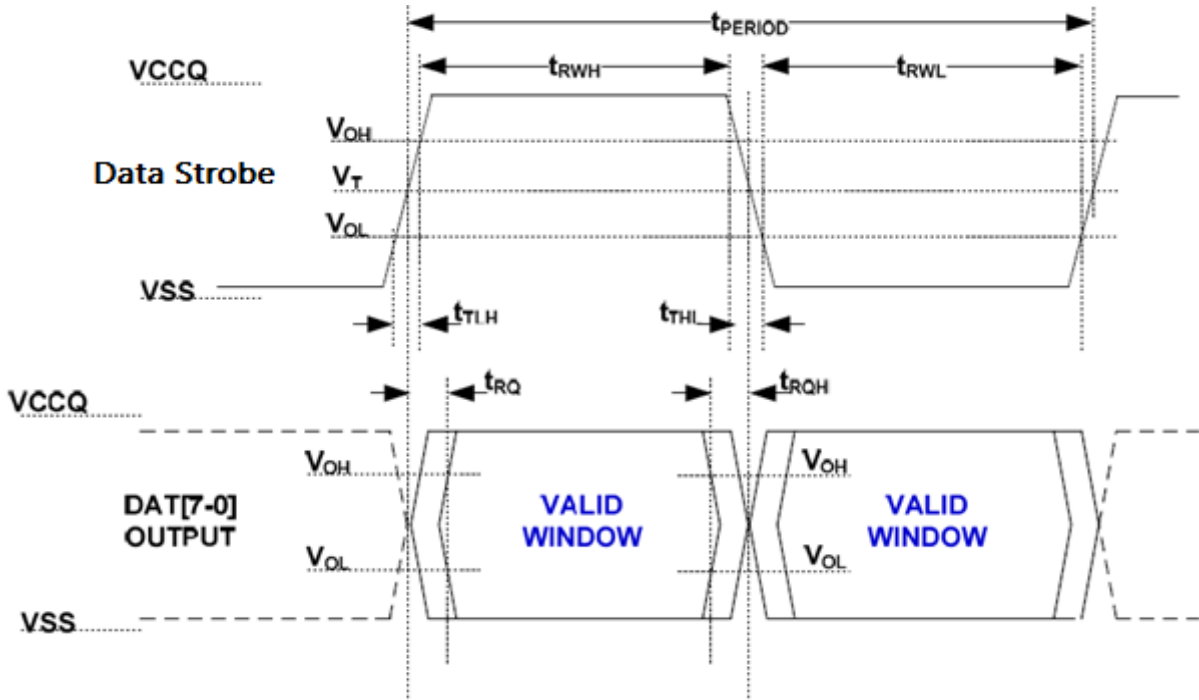


**HS400 Device Input Timing**

**HS400 Device Input Timing**

Parameter	Symbol	Min	Max	Unit	Remark
<b>Input CLK</b>					
Cycle time data transfer mode	$t_{PERIOD}$	5			200MHz(Max), between rising edges With respect to $V_T$ .
Slew rate	SR	1.125		V/ns	With respect to $V_T$
Duty cycle distortion	$t_{CKDCD}$	0.0	0.3	ns	Allowable deviation from an ideal 50% duty cycle. With respect to $V_T$ . Includes jitter, phase noise
Minimum pulse width	$t_{CKMPW}$	2.2		ns	With respect to $V_T$ .
<b>Input DAT (referenced to CLK)</b>					
Input set-up time	$t_{SUDDR}$	0.4		ns	$C_{Device} \leq 6pF$ With respect to $V_{IH}/V_{IL}$ .
Input hold time	$t_{HDDR}$	0.4		ns	$C_{Device} \leq 6pF$ With respect to $V_{IH}/V_{IL}$ .
Slew rate	SR	1.125		V/ns	With respect to $V_{IH}/V_{IL}$ .

HS400 Output Timing



Note:  $V_{OH}$  denotes  $V_{OH(min.)}$  and  $V_{OL}$  denotes  $V_{OL(max.)}$ .

**HS400 Device Output Timing**

## HS400 Device Output Timing

Parameter	Symbol	Min	Max	Unit	Remark
<b>Data Strobe</b>					
Cycle time data transfer mode	$t_{PERIOD}$	5		V/ns	200MHz(Max), between rising edges With respect to $V_T$
Slew rate	SR	1.125		V/ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load
Duty cycle distortion	$t_{DSDCD}$	0.0	0.2	ns	Allowable deviation from the input CLK timing. With respect to $V_T$ Includes jitter, phase noise
Minimum pulse width	$t_{DSMPW}$	2.0		ns	With respect to $V_T$
Read pre-amble	$t_{RPRE}$	0.4	-	$t_{PERIOD}$	Max value is specified by manufacturer. Value up to infinite is valid
Read post-amble	$t_{RPST}$	0.4	-	$t_{PERIOD}$	Max value is specified by manufacturer. Value up to infinite is valid
<b>Output DAT (referenced to Data Strobe)</b>					
Output skew	$t_{RQ}$		0.4	ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load
Output hold skew	$t_{RQH}$		0.4	ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load.
Slew rate	SR	1.125		V/ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load

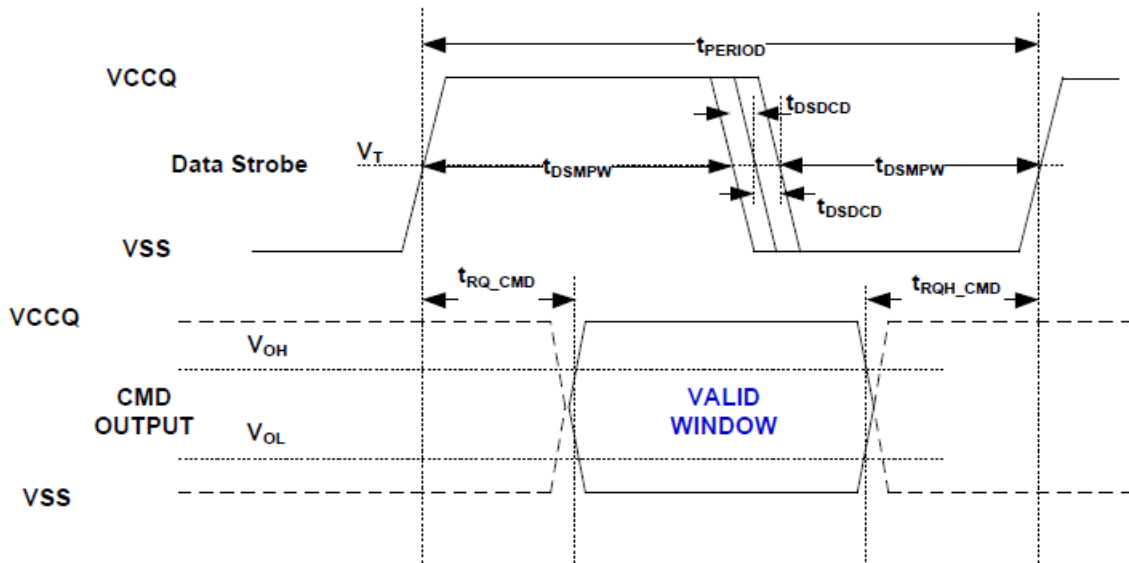
## HS400 Capacitance

Parameter	Symbol	Min	Typ	Max	Unit	Remark
Pull-up resistance for CMD	$R_{CMD}$	4.7		100	KOhm	
Pull-up resistance for DAT0-DAT7	$R_{DAT}$	10		100	KOhm	
Pull-down resistance for Data Strobe	$R_{DS}$	10		100	Kohm	
Internal pull up resistance DAT1-DAT7	$R_{int}$	10		150	KOhm	
Single Device capacitance	$C_{Device}$			6	pF	



**HS400 Device Command Output Timing**

The Data Strobe is used to response of any command in HS400 mode.



Note:  $V_T = 50\%$  of  $V_{CCQ}$ , indicates clock reference point for timing measurements.

**HS400 CMD Response timing**

**HS400 CMD Response timing**

Parameter	Symbol	Min	Max	Unit	Remark
<b>Data Strobe</b>					
Cycle time data transfer mode	$t_{PERIOD}$	5		V/ns	200MHz(Max), between rising edges With respect to $V_T$
Slew rate	SR	1.125		V/ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load
Duty cycle distortion	$t_{DSDCD}$	0.0	0.2	ns	Allowable deviation from the input CLK timing. With respect to $V_T$ Includes jitter, phase noise
Minimum pulse width	$t_{DSMPW}$	2.0		ns	With respect to $V_T$
Read pre-amble	$t_{RPRE}$	0.4	-	$t_{PERIOD}$	Max value is specified by manufacturer. Value up to infinite is valid
Read post-amble	$t_{RPST}$	0.4	-	$t_{PERIOD}$	Max value is specified by manufacturer. Value up to infinite is valid
<b>CMD Response (referenced to Data Strobe)</b>					
Output skew	$t_{RQ}$		0.4	ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load
Output hold skew	$t_{RQH}$		0.4	ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load.
Slew rate	SR	1.125		V/ns	With respect to $V_{OH}/V_{OL}$ and HS400 reference load

## eMMC DC Parameter

### Supply Voltage

Item	Min	Max	Unit
V <sub>CCQ</sub>	1.70(2.7)	1.95(3.6)	V
V <sub>CC</sub>	2.7	3.6	V
V <sub>SS</sub>	-0.5	0.5	V

### Power Consumption

Power Consumption	V <sub>CC</sub> = 3.3V, V <sub>CCQ</sub> = 1.8V		Unit
	NAND	Controller	
Active power consumption during operation <sup>(1, 2)</sup>	40	130	mA
Lower power mode(stand-by)	70	100	uA
Lower power mode(sleep) <sup>(3)</sup>	0	100	uA

Note:

1. Test condition: MAX RMS current @HS400(8bit, 200MHz, DDR), measured on internal board, 25°C
2. In sleep state, triggered by CMD5. Flash V<sub>CC</sub> power supply is switched off.

### Bus Signal Line Load

Paramter	Symbol	Min	Typ.	Max	Unit	Remark
Pull-up resistance for CMD	R <sub>CMD</sub>	4.7		100	KOhm	to prevent bus floating
Pull-up resistance for DAT0-DAT7	R <sub>DAT</sub>	10		100	KOhm	to prevent bus floating
Internal pull up resistance DAT1-DAT7	R <sub>int</sub>	10		150	KOhm	to prevent unconnected lines floating
Bus signal line capacitance	CL			13	pF	Single Device
Single Device capacitance	C <sub>DEVICE</sub>			6	pF	
Pull-down resistance for Data Strobe	R <sub>Data Strobe</sub>	10		100	Kohm	

For 2.7 V - 3.6 V  $V_{CCQ}$  range (compatible with JESD8C.01)

### Push-pull signal level - high-voltage

Parameter	Symbol	Min	Max	Unit	Conditions
Output HIGH voltage	$V_{OH}$	$0.75 * V_{CCQ}$		V	$I_{OH} = -100 \mu A @ V_{CCQ} \text{ min}$
Output LOW voltage	$V_{OL}$		$0.125 * V_{CCQ}$	V	$I_{OL} = 100 \mu A @ V_{CCQ} \text{ min}$
Input HIGH voltage	$V_{IH}$	$0.625 * V_{CCQ}$	$V_{CCQ} + 0.3$	V	
Input LOW voltage	$V_{IL}$	$V_{SS} - 0.3$	$0.25 * V_{CCQ}$	V	

For 1.70V - 1.95V  $V_{CCQ}$  range

### Push-pull signal level - 1.70V-1.95V $V_{CCQ}$ voltage range

Parameter	Symbol	Min	Max	Unit	Conditions
Output HIGH voltage	$V_{OH}$	$V_{CCQ} - 0.45$		V	$I_{OH} = -2mA$
Output LOW voltage	$V_{OL}$		0.45	V	$I_{OL} = 2mA$
Input HIGH voltage	$V_{IH}$	$0.65 * V_{CCQ}^{(1)}$	$V_{CCQ} + 0.3$	V	
Input LOW voltage	$V_{IL}$	$V_{SS} - 0.3$	$0.35 * V_{CCQ}^{(2)}$	V	

Note:

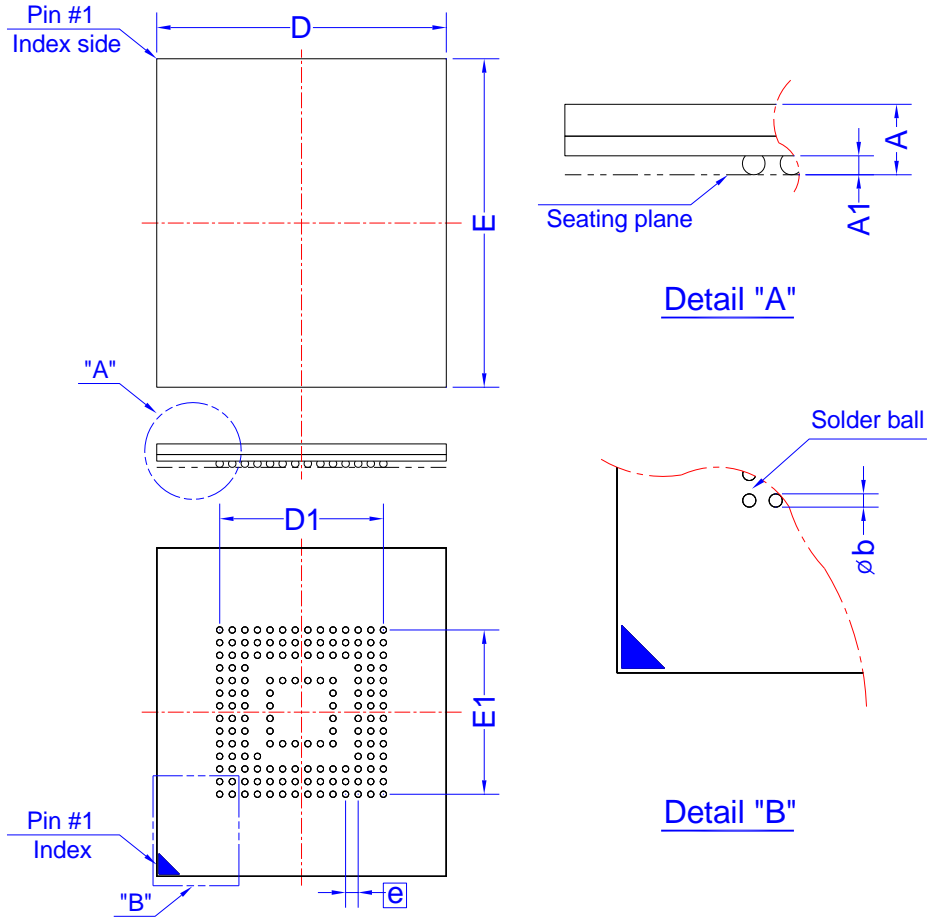
1.  $0.7 * V_{DD}$  for MMC4.3 and older revisions.
2.  $0.3 * V_{DD}$  for MMC4.3 and older revisions.

## PACKING

## DIMENSIONS

153-BALL

( 11.5x13 mm )



Symbol	Dimension in mm			Dimension in inch		
	Min	Norm	Max	Min	Norm	Max
A	—	—	1.00	—	—	0.039
A <sub>1</sub>	0.16	0.21	0.26	0.006	0.008	0.010
Φ <sub>b</sub>	0.25	0.30	0.35	0.010	0.012	0.014
D	11.40	11.50	11.60	0.449	0.453	0.457
E	12.90	13.00	13.10	0.508	0.512	0.516
D <sub>1</sub>	6.50 BSC			0.256 BSC		
E <sub>1</sub>	6.50 BSC			0.256 BSC		
e	0.50 BSC			0.020 BSC		

Controlling dimension : Millimeter.

(Revision date : Jun 14 2017)

**Revision History**

Revision	Date	Description
0.1	2021.01.11	Original
0.2	2022.01.14	1. Modify the ball name of VDDIM, RDT_n and DS 2. Modify High-Speed & Backward Compatible Device Interface Timing table 3. Correct the note of High-speed Dual Data Rate Interface Timing table
0.3	2022.03.31	1. Modify Density 2. Modify Ext-CSD [184], Ext-CSD [215:212] value
1.0	2022.04.22	Delete Preliminary

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